AMENDMENT
Serial Number: 10/053.300
Docket No: 303.780US1

Serial Number: 10/053,300 Filing Date: January 17, 2002

Title: TRANSISTOR STRUCTURE HAVING REDUCED TRANSISTOR LEAKAGE ATTRIBUTES

## **IN THE SPECIFICATION**

## The paragraph beginning at page 10, line 2 is amended as follows:

Such removal of the second and first layers, unfortunately, often leaves a "dip" where third layer 650 plugs trench 618. A technique for overcoming this problem, that can be utilized with the teachings of this invention, is described in a related, co-pending, commonly assigned, U.S. patent application "Isolation Region Forming Methods," attorney docket no. MI22-930, Serial No. 09/146,838, filed on [[\_\_\_\_\_\_]] September 3, 1998, now U.S. Patent No. 6,372,601, and herein incorporated by reference.

## **CONCLUSION**

Applicant respectfully submits that the claims are in condition for allowance and notification to that effect is earnestly requested. The Examiner is invited to telephone Applicant's attorney at (612) 373-6904 to facilitate prosecution of this application.

If necessary, please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

Respectfully Submitted,

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By their Representatives,

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CERTIFICATE UNDER 37 CFR § 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelop addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 16 day of December 2004.

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